Low-Voltage CMOS Octal Buffer Flow Through Pinout

With 5V-Tolerant Inputs and Outputs (3-State, Inverting)

The MC74LCX540 is a high performance, inverting octal buffer operating from a 2.3 to 3.6V supply. This device is similar in function to the MC74LCX240, while providing flow through architecture. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A $V_{\rm I}$ specification of 5.5V allows MC74LCX540 inputs to be safely driven from 5V devices. The MC74LCX540 is suitable for memory address driving and all TTL level bus oriented transceiver applications.

Current drive capability is 24mA at the outputs. The Output Enable $(\overline{OE1}, \overline{OE2})$ inputs, when HIGH, disables the outputs by placing them in a HIGH Z condition.

- \bullet Designed for 2.3 to 3.6V V_{CC} Operation
- 5V Tolerant Interface Capability With 5V TTL Logic
- Supports Live Insertion and Withdrawal
- I_{OFF} Specification Guarantees High Impedance When $V_{CC} = 0V$
- LVTTL Compatible
- LVCMOS Compatible
- 24mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current in All Three Logic States (10μA) Substantially Reduces System Power Requirements
- Latchup Performance Exceeds 500mA
- ESD Performance: Human Body Model >2000V; Machine Model >200V

MC74LCX540



LOW-VOLTAGE CMOS OCTAL BUFFER



DW SUFFIX PLASTIC SOIC CASE 751D-04



M SUFFIX
PLASTIC SOIC EIAJ
CASE 967-01



DT SUFFIXPLASTIC TSSOP
CASE 948E-02

PIN NAMES

Pins	Function
OEn	Output Enable Inputs
Dn	Data Inputs
On	3–State Outputs

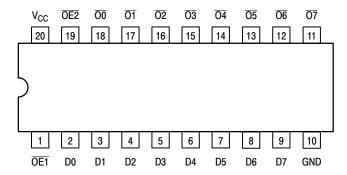


Figure 1. Pinout: 20-Lead (Top View)

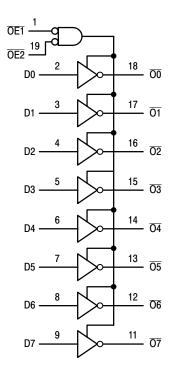


Figure 2. LOGIC DIAGRAM

INPUTS			OUTPUTS
OE1	OE2	Dn	On
L	L	L	Н
L	L	Н	L
Х	Н	Х	Z
Н	Х	Х	Z

 $H=\mbox{High Voltage Level; }L=\mbox{Low Voltage Level; }Z=\mbox{High Impedance State; }X=\mbox{High or Low Voltage Level and Transitions Are Acceptable, for <math display="inline">I_{CC}$ reasons, DO NOT FLOAT Inputs

ABSOLUTE MAXIMUM RATINGS*

Symbol	Parameter	Value	Condition	Unit
V _{CC}	DC Supply Voltage	-0.5 to +7.0		V
VI	DC Input Voltage	$-0.5 \le V_1 \le +7.0$		V
Vo	DC Output Voltage	$-0.5 \le V_O \le +7.0$	Output in 3-State	V
		$-0.5 \le V_{O} \le V_{CC} + 0.5$	Note 1.	V
I _{IK}	DC Input Diode Current	-50	V _I < GND	mA
I _{OK}	DC Output Diode Current	-50	V _O < GND	mA
		+50	$V_O > V_{CC}$	mA
I _O	DC Output Source/Sink Current	±50		mA
I _{CC}	DC Supply Current Per Supply Pin	±100		mA
I _{GND}	DC Ground Current Per Ground Pin	±100		mA
T _{STG}	Storage Temperature Range	-65 to +150		°C

^{*} Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute—maximum—rated conditions is not implied.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Тур	Max	Unit
Vcc	Supply Voltage Operating Data Retention Only	2.0 1.5	3.3 3.3	3.6 3.6	٧
V _I	Input Voltage	0		5.5	V
Vo	Output Voltage (HIGH or LOW State) (3–State)	0 0		V _{CC} 5.5	٧
I _{OH}	HIGH Level Output Current, V _{CC} = 3.0V – 3.6V			-24	mA
I _{OL}	LOW Level Output Current, V _{CC} = 3.0V – 3.6V			24	mA
I _{OH}	HIGH Level Output Current, V _{CC} = 2.7V – 3.0V			-12	mA
I _{OL}	LOW Level Output Current, V _{CC} = 2.7V - 3.0V			12	mA
T _A	Operating Free–Air Temperature	-40		+85	°C
Δt/ΔV	Input Transition Rise or Fall Rate, V_{IN} from 0.8V to 2.0V, $V_{CC} = 3.0V$	0		10	ns/V

DC ELECTRICAL CHARACTERISTICS

			T _A = -40°C	to +85°C	
Symbol	Characteristic	Condition	Min	Max	Unit
V _{IH}	HIGH Level Input Voltage (Note 2.)	2.7V ≤ V _{CC} ≤ 3.6V	2.0		V
V _{IL}	LOW Level Input Voltage (Note 2.)	2.7V ≤ V _{CC} ≤ 3.6V		0.8	V
V _{OH}	HIGH Level Output Voltage	$2.7V \le V_{CC} \le 3.6V; I_{OH} = -100\mu A$	V _{CC} - 0.2		V
		$V_{CC} = 2.7V; I_{OH} = -12mA$	2.2		1
		$V_{CC} = 3.0V; I_{OH} = -18mA$	2.4]
		$V_{CC} = 3.0V; I_{OH} = -24mA$	2.2		1
V _{OL}	LOW Level Output Voltage	$2.7V \le V_{CC} \le 3.6V; I_{OL} = 100\mu A$		0.2	V
		V _{CC} = 2.7V; I _{OL} = 12mA		0.4	
		V _{CC} = 3.0V; I _{OL} = 16mA		0.4]
		V _{CC} = 3.0V; I _{OL} = 24mA		0.55	

^{2.} These values of V_I are used to test DC electrical characteristics only.

^{1.} Output in HIGH or LOW State. $I_{\rm O}$ absolute maximum rating must be observed.

DC ELECTRICAL CHARACTERISTICS (continued)

			$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$		
Symbol	Characteristic	Condition	Min	Max	Unit
I _I	Input Leakage Current	$2.7V \le V_{CC} \le 3.6V$; $0V \le V_{I} \le 5.5V$		±5.0	μΑ
I _{OZ}	3-State Output Current	$2.7 \le V_{CC} \le 3.6V$; $0V \le V_O \le 5.5V$; $V_I = V_{IH}$ or V_{IL}		±5.0	μΑ
I _{OFF}	Power-Off Leakage Current	$V_{CC} = 0V$; V_I or $V_O = 5.5V$		10	μΑ
I _{CC}	Quiescent Supply Current	$2.7 \le V_{CC} \le 3.6V$; $V_I = GND \text{ or } V_{CC}$		10	μΑ
		$2.7 \le V_{CC} \le 3.6V$; $3.6 \le V_I$ or $V_O \le 5.5V$		±10	μΑ
Δl _{CC}	Increase in I _{CC} per Input	$2.7 \le V_{CC} \le 3.6V$; $V_{IH} = V_{CC} - 0.6V$		500	μΑ

AC CHARACTERISTICS ($t_R = t_F = 2.5 ns$; $C_L = 50 pF$; $R_L = 500 \Omega$)

				Limits		
			T,	_A = -40°C to	+85°C	
			V _{CC} = 3.0	OV to 3.6V	V _{CC} = 2.7V	
Symbol	Parameter	Waveform	Min	Max	Max	Unit
t _{PLH} t _{PHL}	Propagation Delay Input to Output	1	1.5 1.5	6.5 6.5	7.5 7.5	ns
t _{PZH} t _{PZL}	Output Enable Time to High and Low Level	2	1.5 1.5	8.5 8.5	9.5 9.5	ns
t _{PHZ}	Output Disable Time From High and Low Level	2	1.5 1.5	7.5 7.5	8.5 8.5	ns
toshl toslh	Output-to-Output Skew (Note 3.)			1.0 1.0		ns

Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device.
 The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.

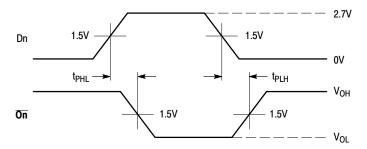
DYNAMIC SWITCHING CHARACTERISTICS

			T _A = +25°C			
Symbol	Characteristic	Condition	Min	Тур	Max	Unit
V _{OLP}	Dynamic LOW Peak Voltage (Note 4.)	$V_{CC} = 3.3V$, $C_L = 50pF$, $V_{IH} = 3.3V$, $V_{IL} = 0V$		0.8		V
V _{OLV}	Dynamic LOW Valley Voltage (Note 4.)	$V_{CC} = 3.3V$, $C_L = 50pF$, $V_{IH} = 3.3V$, $V_{IL} = 0V$		0.8		V

^{4.} Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

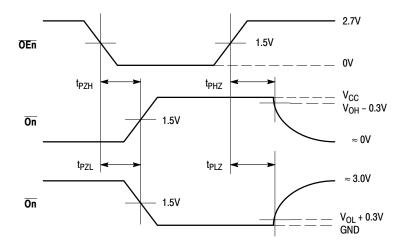
CAPACITIVE CHARACTERISTICS

Symbol	mbol Parameter Condition		Typical	Unit
C _{IN}	Input Capacitance	$V_{CC} = 3.3V$, $V_I = 0V$ or V_{CC}	7	pF
C _{OUT}	Output Capacitance	V_{CC} = 3.3V, V_{I} = 0V or V_{CC}	8	pF
C _{PD}	Power Dissipation Capacitance	10MHz, V_{CC} = 3.3V, V_{I} = 0V or V_{CC}	25	pF



WAVEFORM 1 - PROPAGATION DELAYS

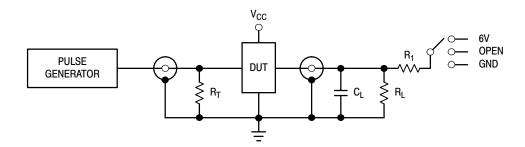
 $t_R = t_F = 2.5$ ns, 10% to 90%; f = 1MHz; $t_W = 500$ ns



WAVEFORM 2 - OUTPUT ENABLE AND DISABLE TIMES

 $t_R = t_F = 2.5$ ns, 10% to 90%; f = 1MHz; $t_W = 500$ ns

Figure 3. AC Waveforms



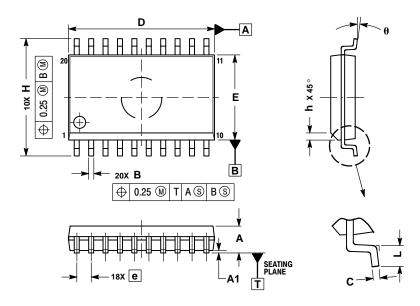
TEST	SWITCH
t _{PLH} , t _{PHL}	Open
t _{PZL} , t _{PLZ}	6V
Open Collector/Drain t _{PLH} and t _{PHL}	6V
t _{PZH} , t _{PHZ}	GND

 $C_L=50pF$ or equivalent (Includes jig and probe capacitance) $R_L=R_1=500\Omega$ or equivalent $R_T=Z_{OUT}$ of pulse generator (typically $50\Omega)$

Figure 4. Test Circuit

OUTLINE DIMENSIONS

DW SUFFIX PLASTIC SOIC PACKAGE CASE 751D-04 ISSUE E



NOTES:

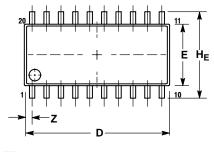
- NOTES:

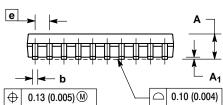
 1. DIMENSIONS ARE IN MILLIMETERS.
 2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
 5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION. MAXIMUM MATERIAL CONDITION.

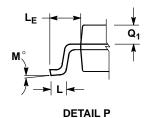
	MILLIMETERS		
DIM	MIN	MAX	
Α	2.35	2.65	
A1	0.10	0.25	
В	0.35	0.49	
С	0.23	0.32	
D	12.65	12.95	
Е	7.40	7.60	
е	1.27	BSC	
Н	10.05	10.55	
h	0.25	0.75	
L	0.50	0.90	
θ	0 °	7 °	

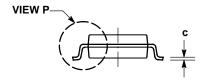
M SUFFIX PLASTIC SOIC EIAJ PACKAGE

CASE 967-01 ISSUE O









NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

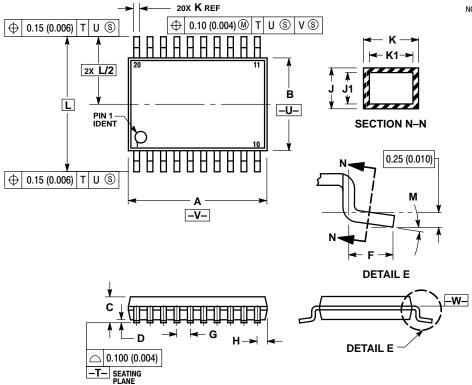
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006)
- PER SIDE.
 TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
 THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH
 DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
С	0.18	0.27	0.007	0.011
D	12.35	12.80	0.486	0.504
E	5.10	5.45	0.201	0.215
е	1.27	BSC	0.050	BSC
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10°	0°	10°
Q ₁	0.70	0.90	0.028	0.035
Z		0.81		0.032

OUTLINE DIMENSIONS

DT SUFFIX

PLASTIC TSSOP PACKAGE CASE 948E-02 ISSUE A



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
- y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD
- FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

 6. TERMINAL NUMBERS ARE SHOWN FOR
- MATERIAL CONDITION.

 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	6.40	6.60	0.252	0.260
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

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